



YJJD05N03A

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	30V
I_D	5.0A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	33mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	55mohm
V_{GS} Tested	

General Description

Trench Power MV MOSFET technology
High Power and current handing capability

Applications

PWM application
Switching, etc.

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250 \text{ } \mu\text{E}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μE
Gate-Body Leakage Current	I_{GSS1}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250 \text{ } \mu\text{E}$	1.0	1.5	2.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3.6$				

Typical Performance Characteristics

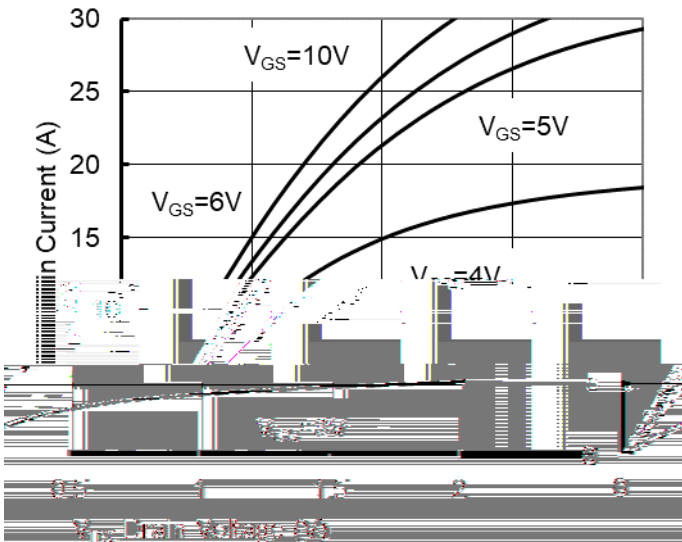


Figure1. Output Characteristics

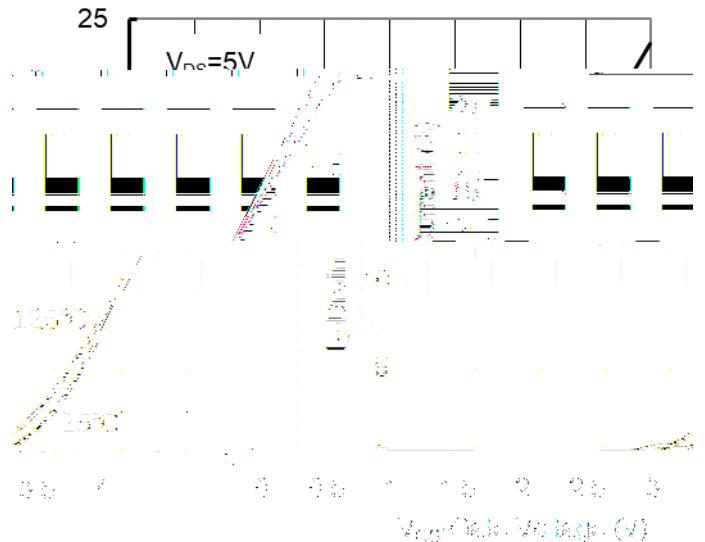


Figure2. Transfer Characteristics

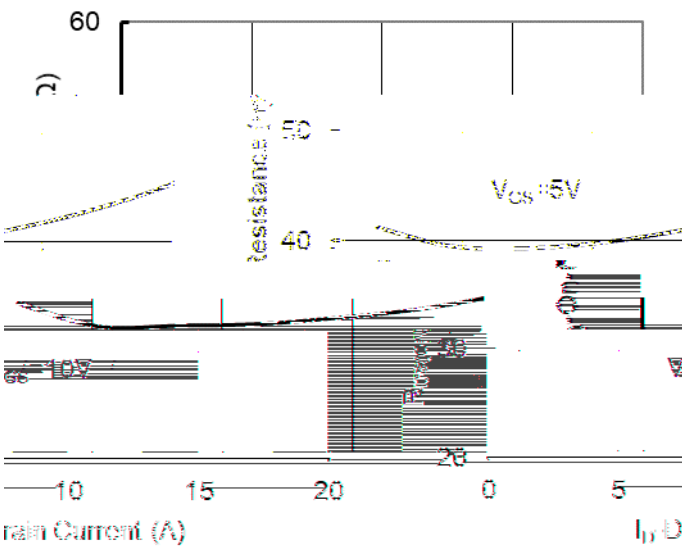


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

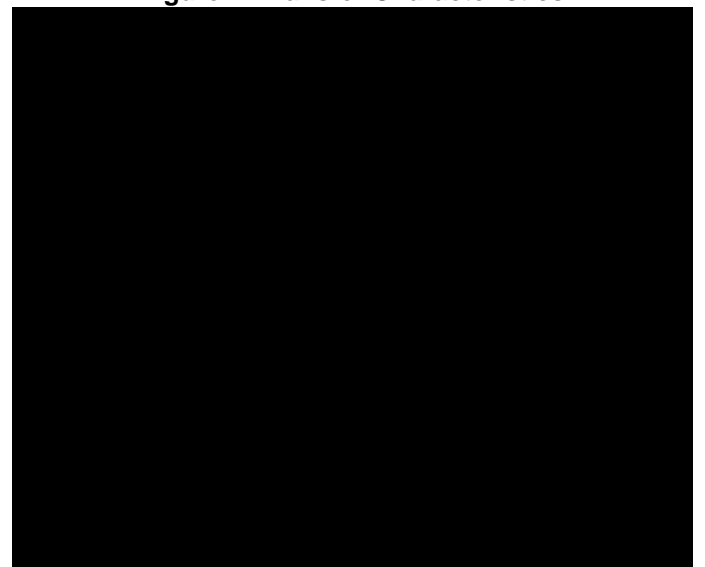


Figure 4: On-Resistance vs. Junction Temperature

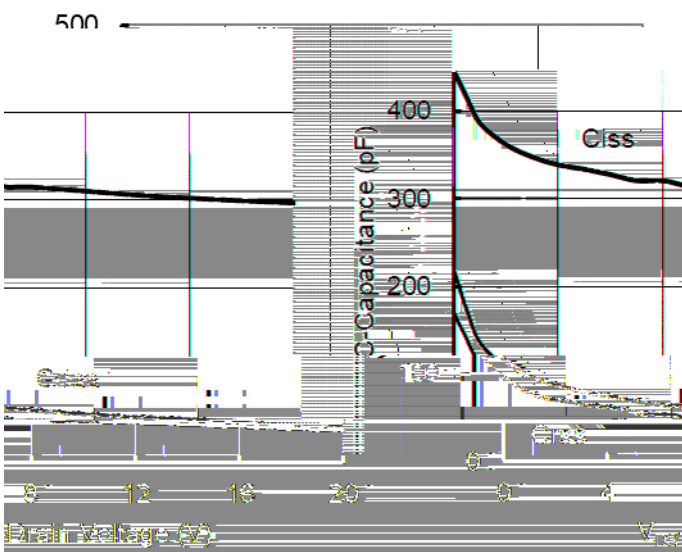


Figure5. Capacitance Characteristics

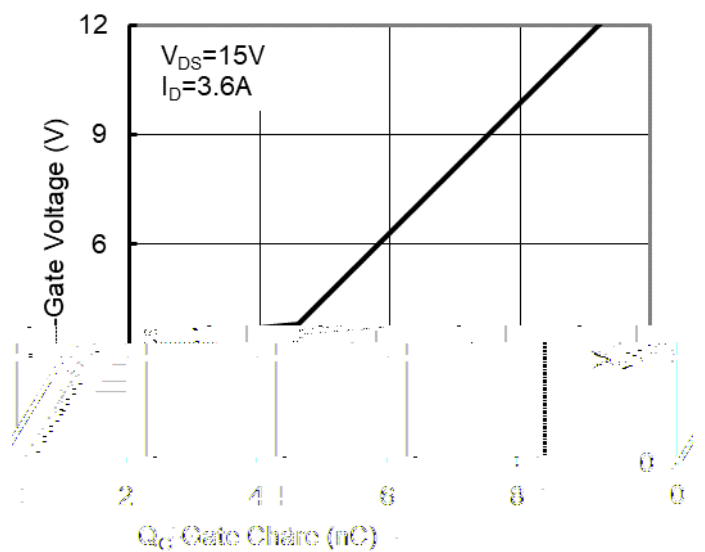


Figure6. Gate Charge

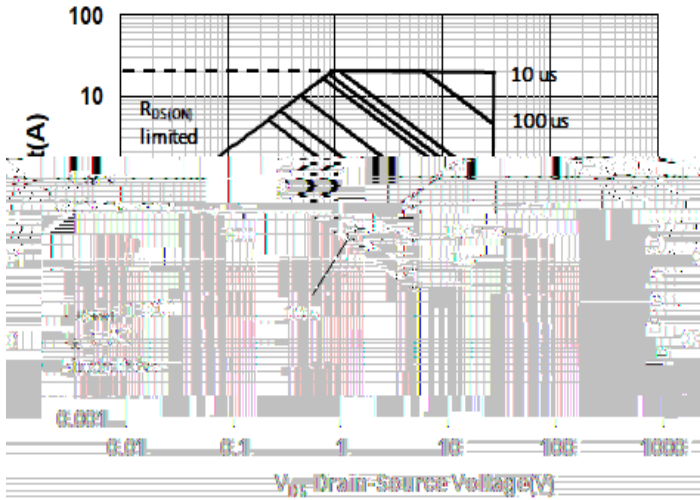


Figure7. Safe Operation Area

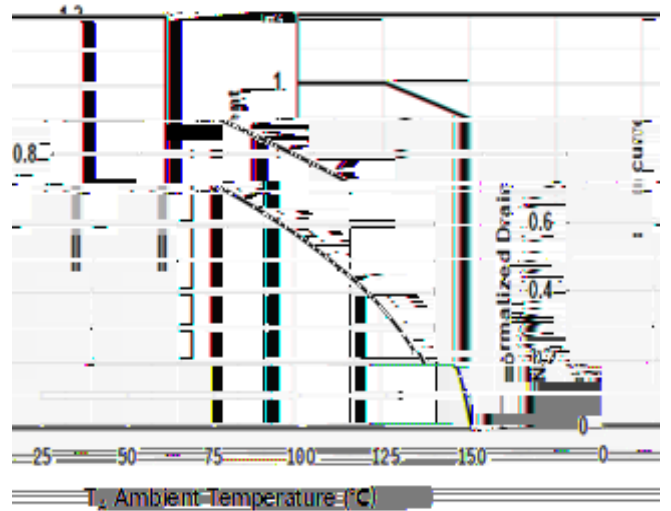
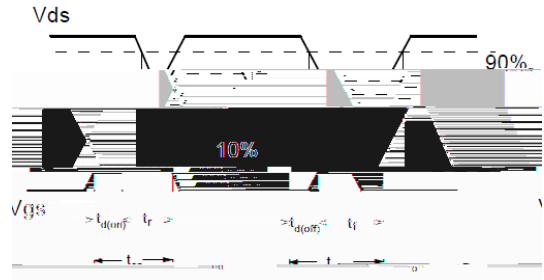
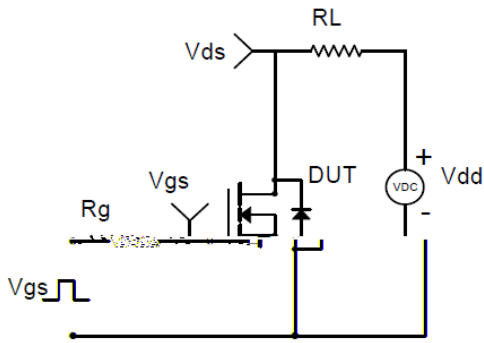


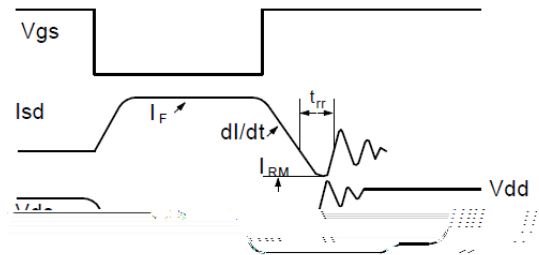
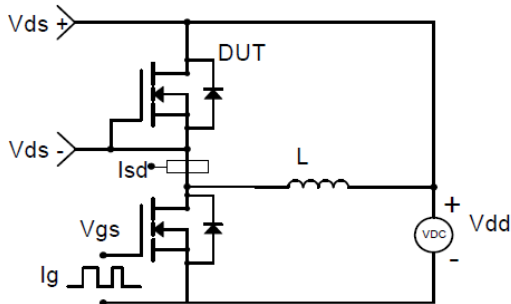
Figure8. Maximum Continuous Drain Current vs Ambient Temperature



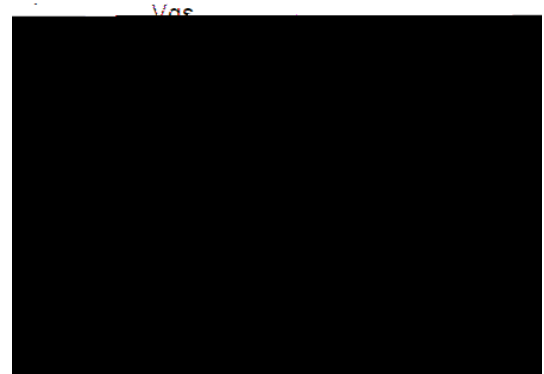
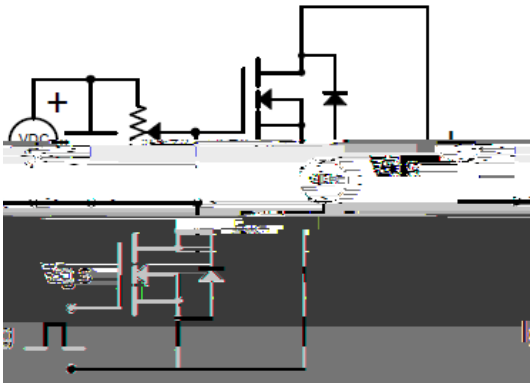
Figure9. Normalized Maximum Transient Thermal Impedance



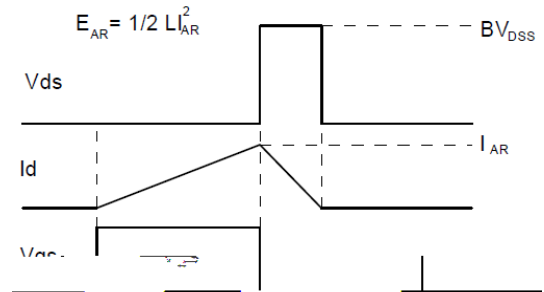
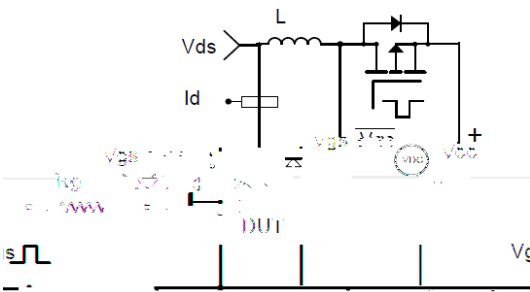
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

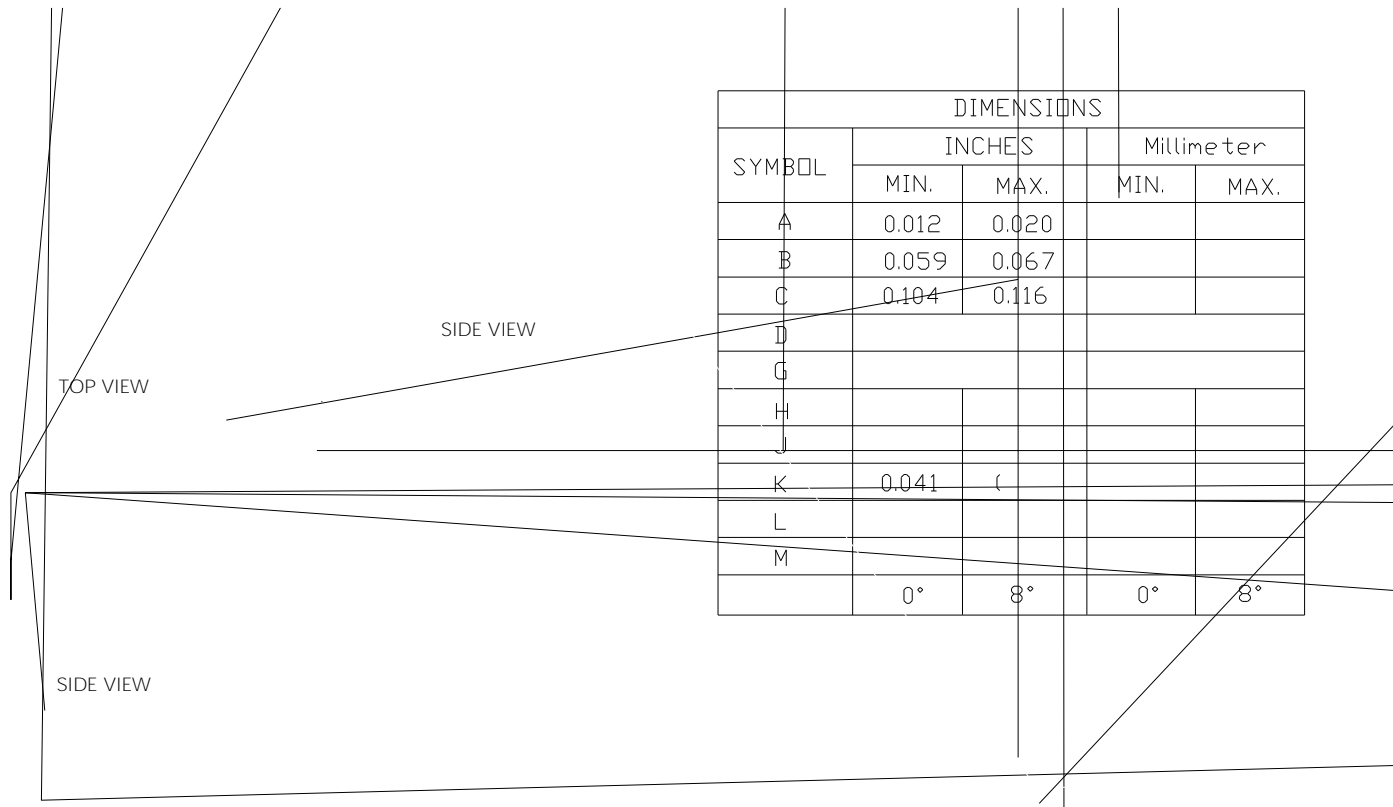


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



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SOT-23-6L Package information





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